

Fig.1

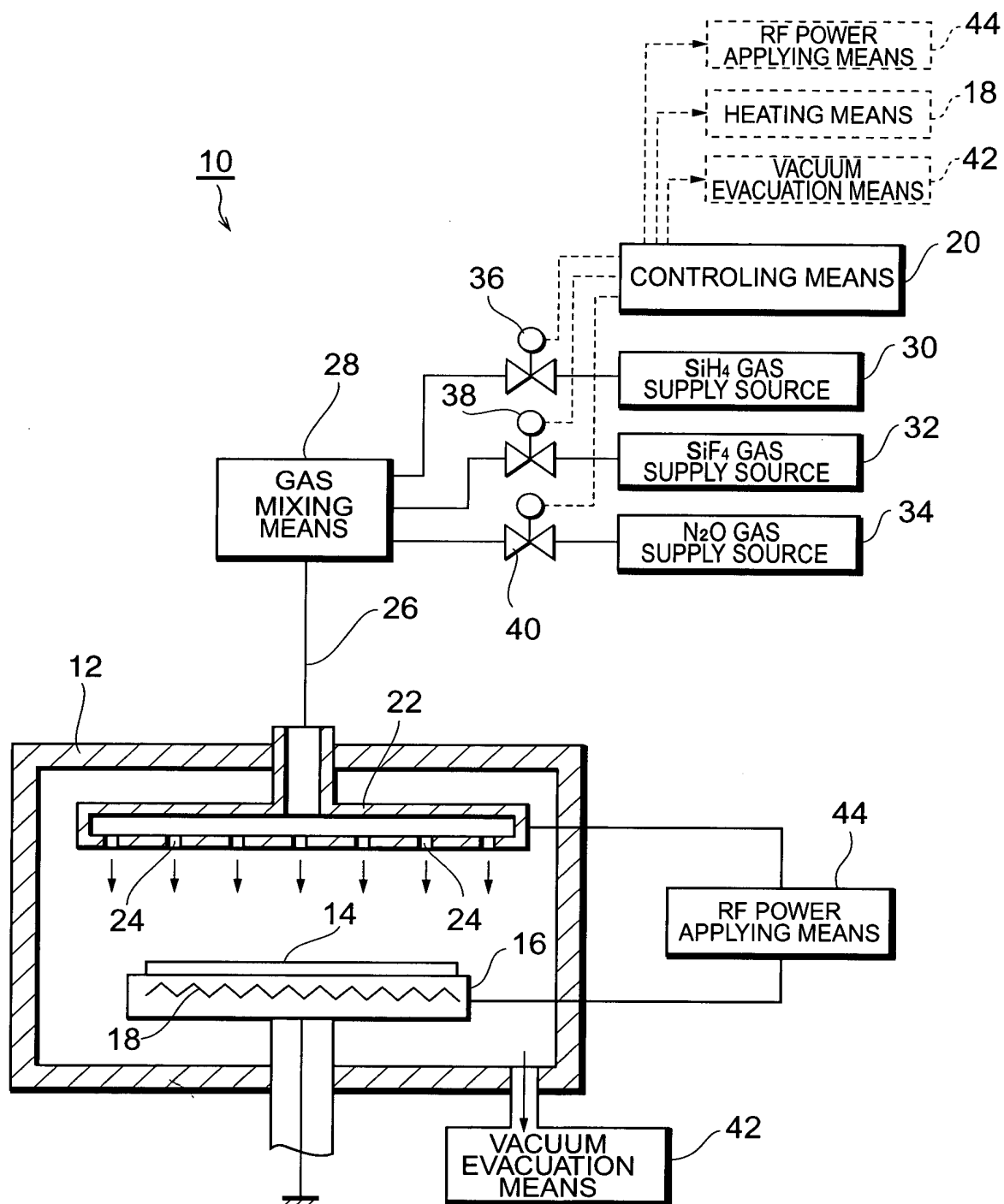


Fig. 2A

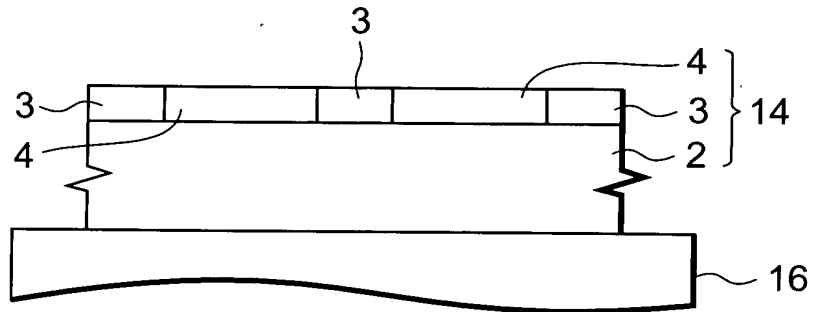


Fig. 2B

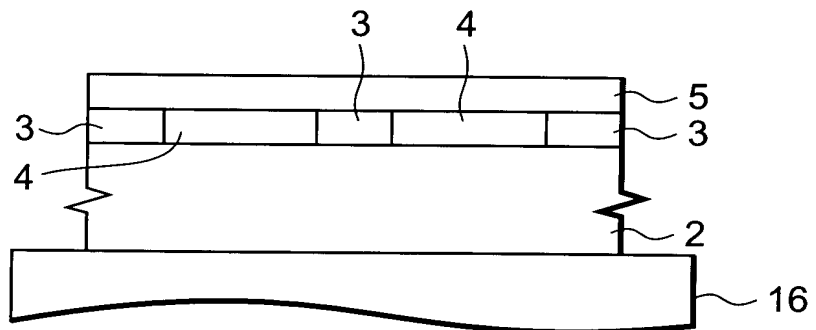


Fig. 2C

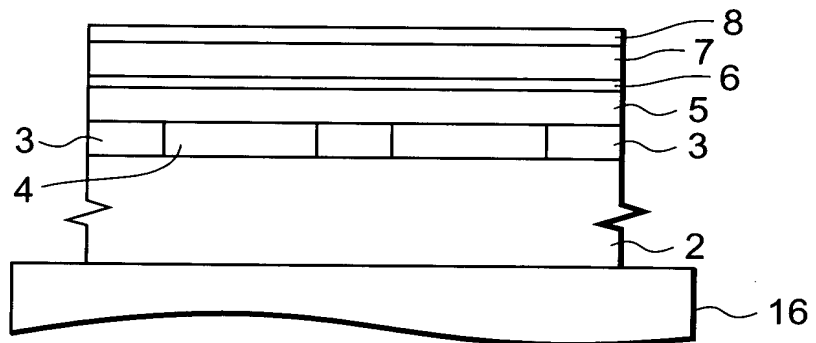


Fig. 2D

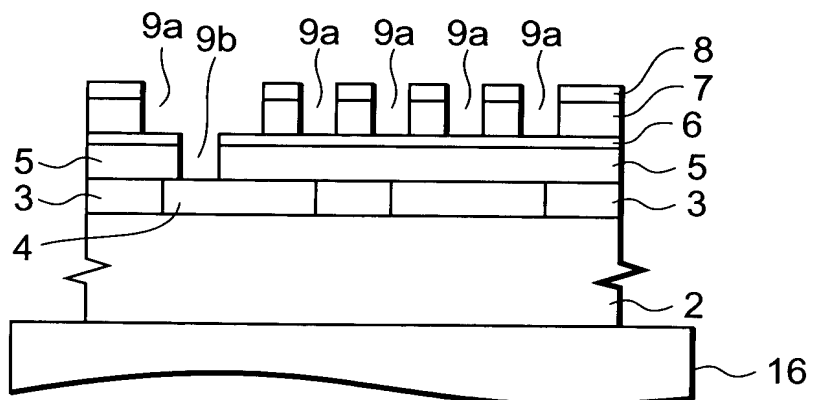


Fig.3

| PARAMETER | TEST CONDITIONS | RAUGE OF VARIATION |
|---|-----------------|-----------------------|
| 13.56MHz RF POWER (W) | 1500 | 1200~2000 |
| PARALLEL PLATE ELECTRODE SEPARATION (cm) | 1.0 | 1.0~1.75 |
| CHAMBER PRESSURE (Pa) | 493 (3.7Torr) | 493~666 (3.7~5.0Torr) |
| TOTAL FLOW VOLUME(%) | 100 | 100~200 |
| N ₂ O FLOW VOLUME (sccm) | 1500 | 1500~3000 |
| SiH ₄ FLOW VOLUME (sccm) | 115 | 115 |
| SiF ₄ FLOW VOLUME (sccm) | 130 | 50~250 |

Fig.4

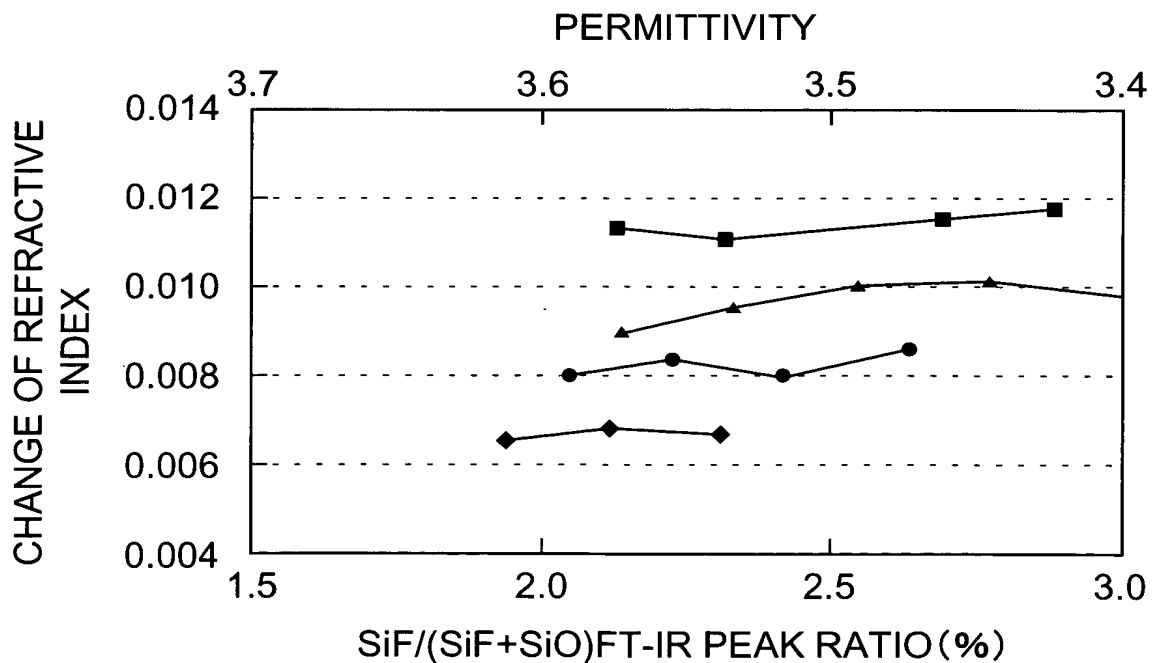


Fig.5

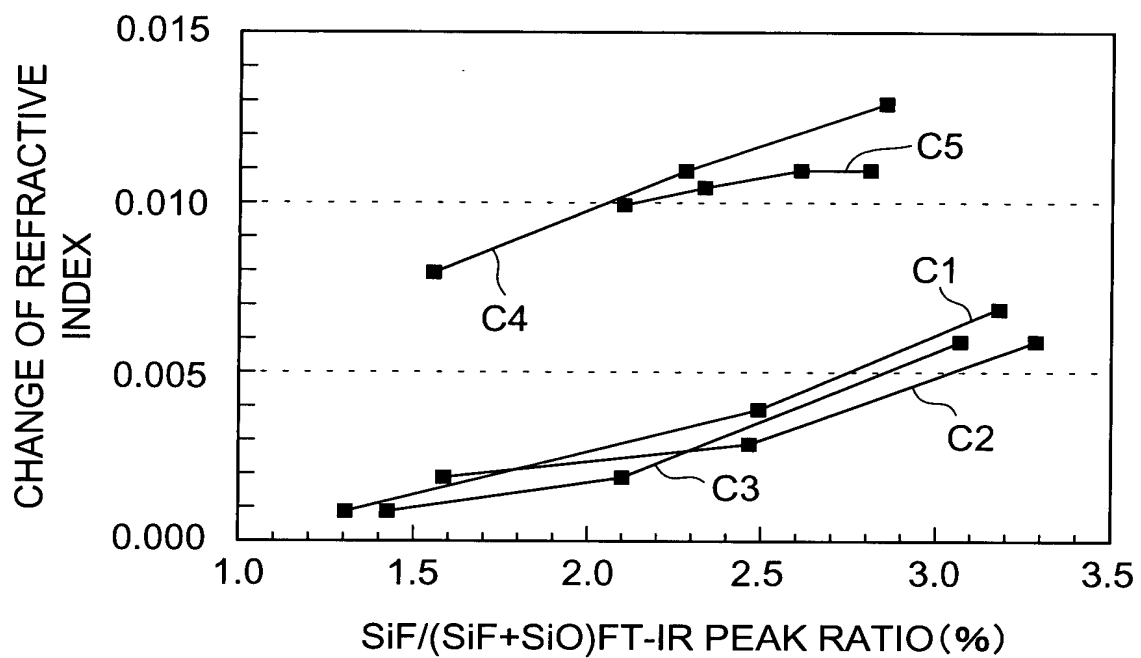


Fig.6

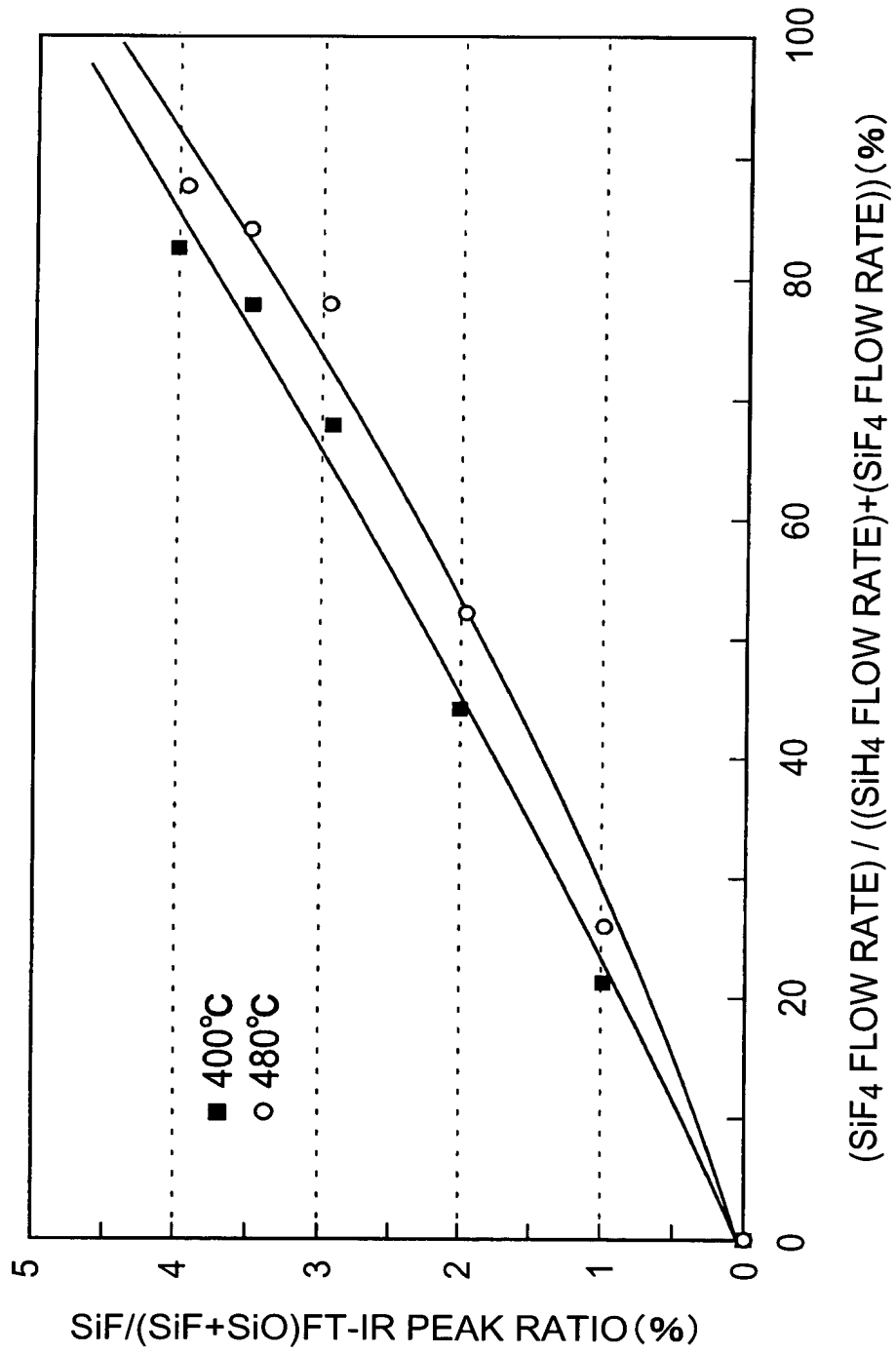


Fig.7

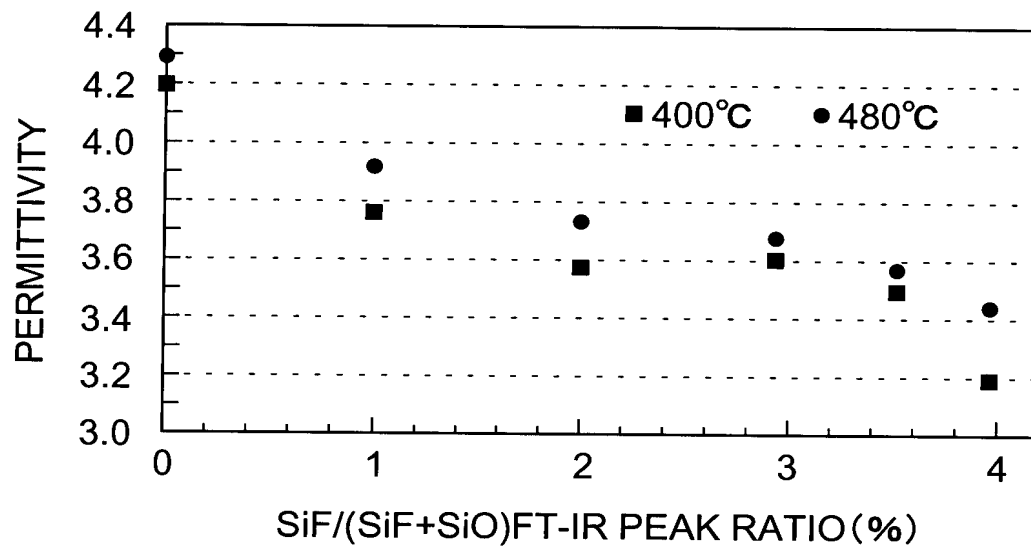


Fig.8

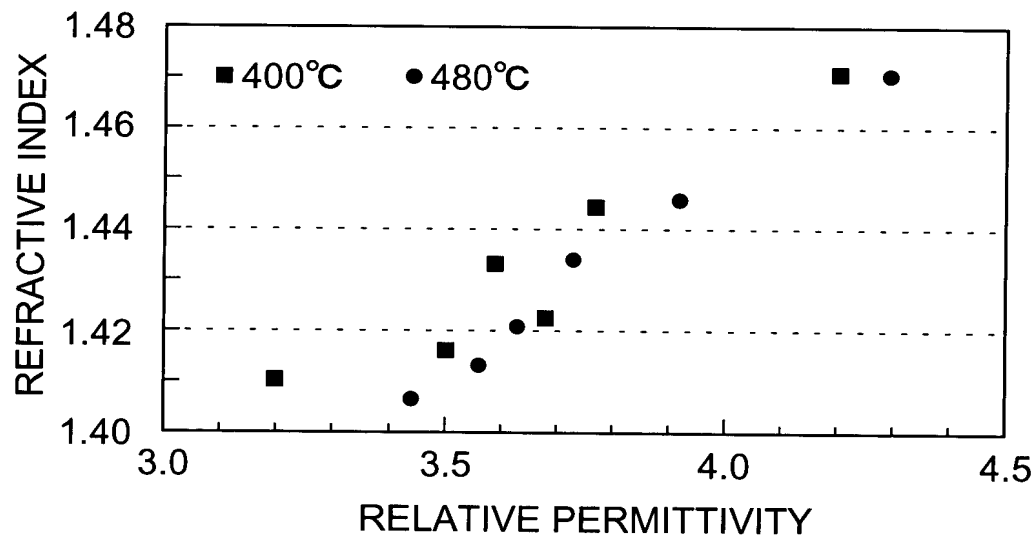


Fig.9

| TYPE OF FILM | | SiH ₄ FSG | | | TEOS FSG |
|---|-----------------------|----------------------|-------|-------|----------|
| FILM FORMING TEMPERAFURE | | 400°C | 440°C | 480°C | 480°C |
| (SiOH+HOH)/SiO PEAK RATIO IN FT-IR AFTER LEFT IN CLEAN ROOM | LEFT FOR ONE WEEK | 0.5 | 0.4 | 1.0 | 2.5 |
| | LEFT FOR TWO WEEKS | 0.7 | 1.1 | 0.7 | — |

Fig. 10

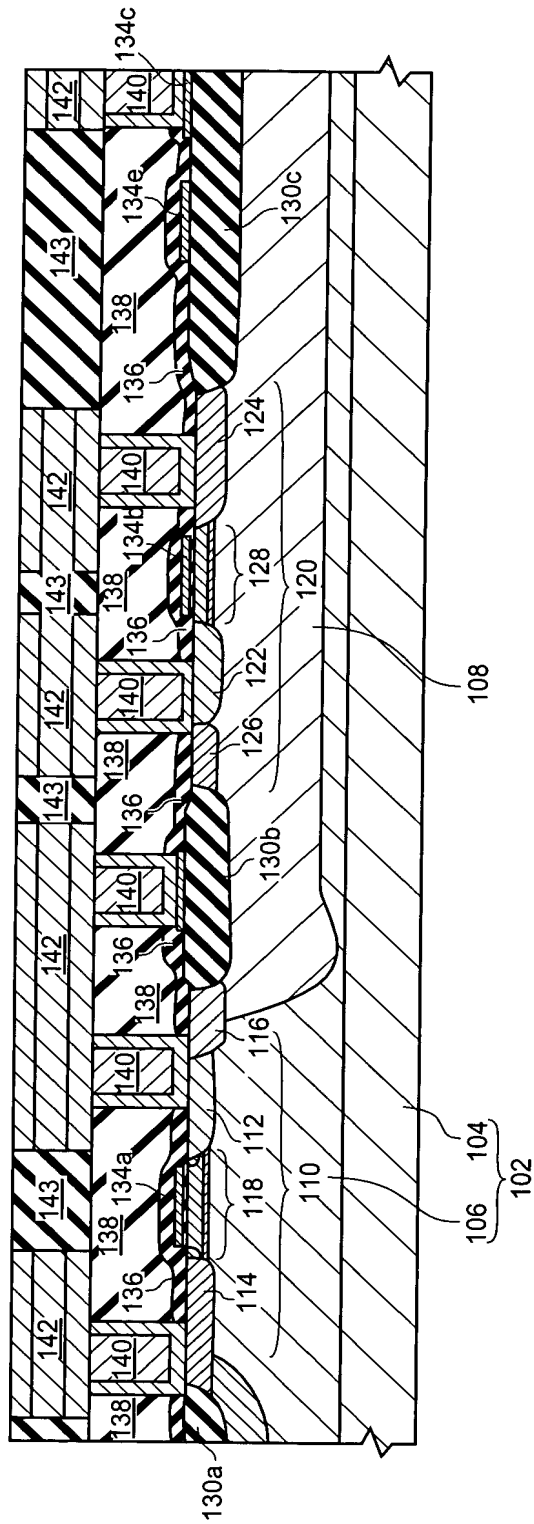


Fig. 11

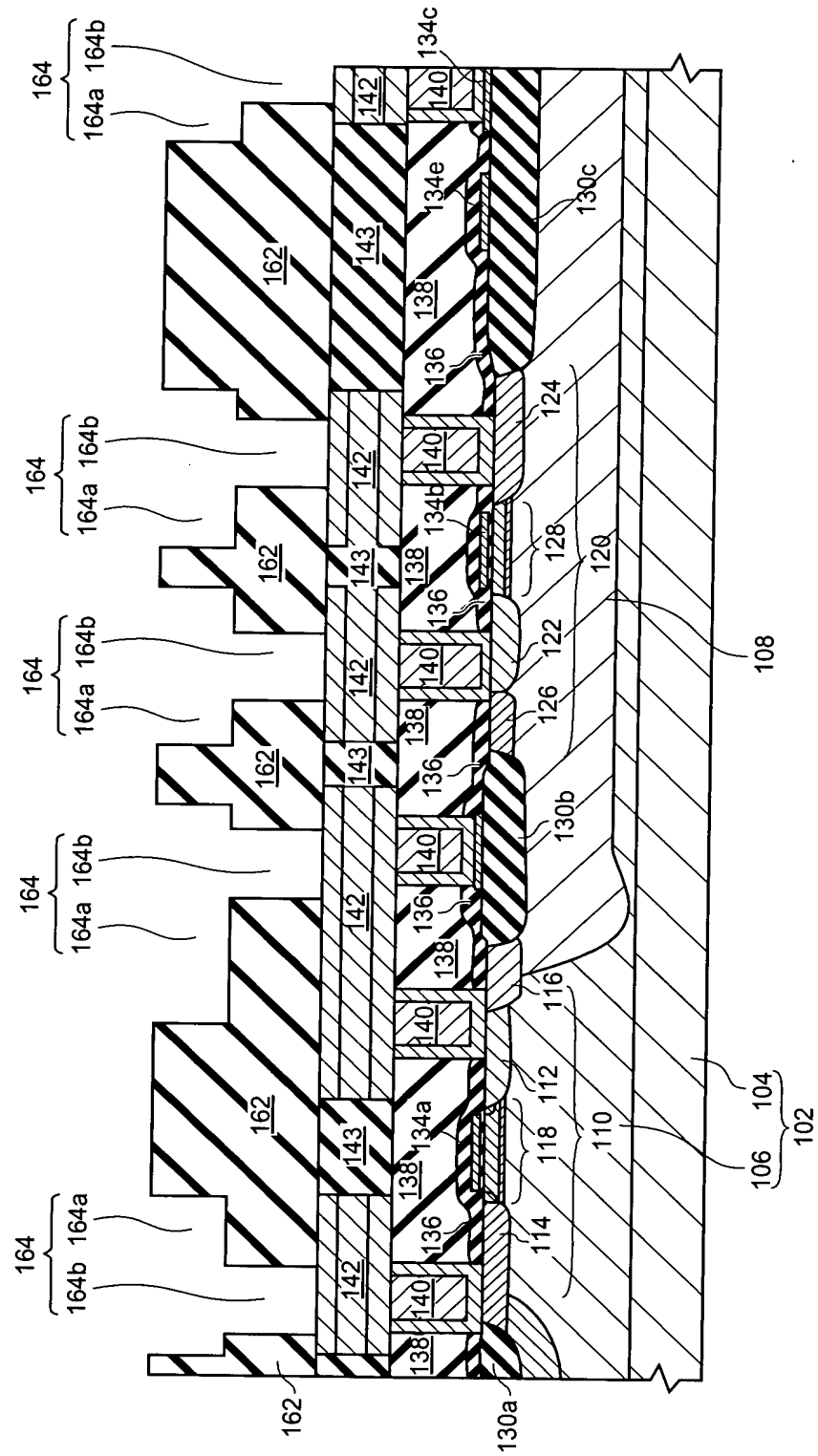


Fig. 13

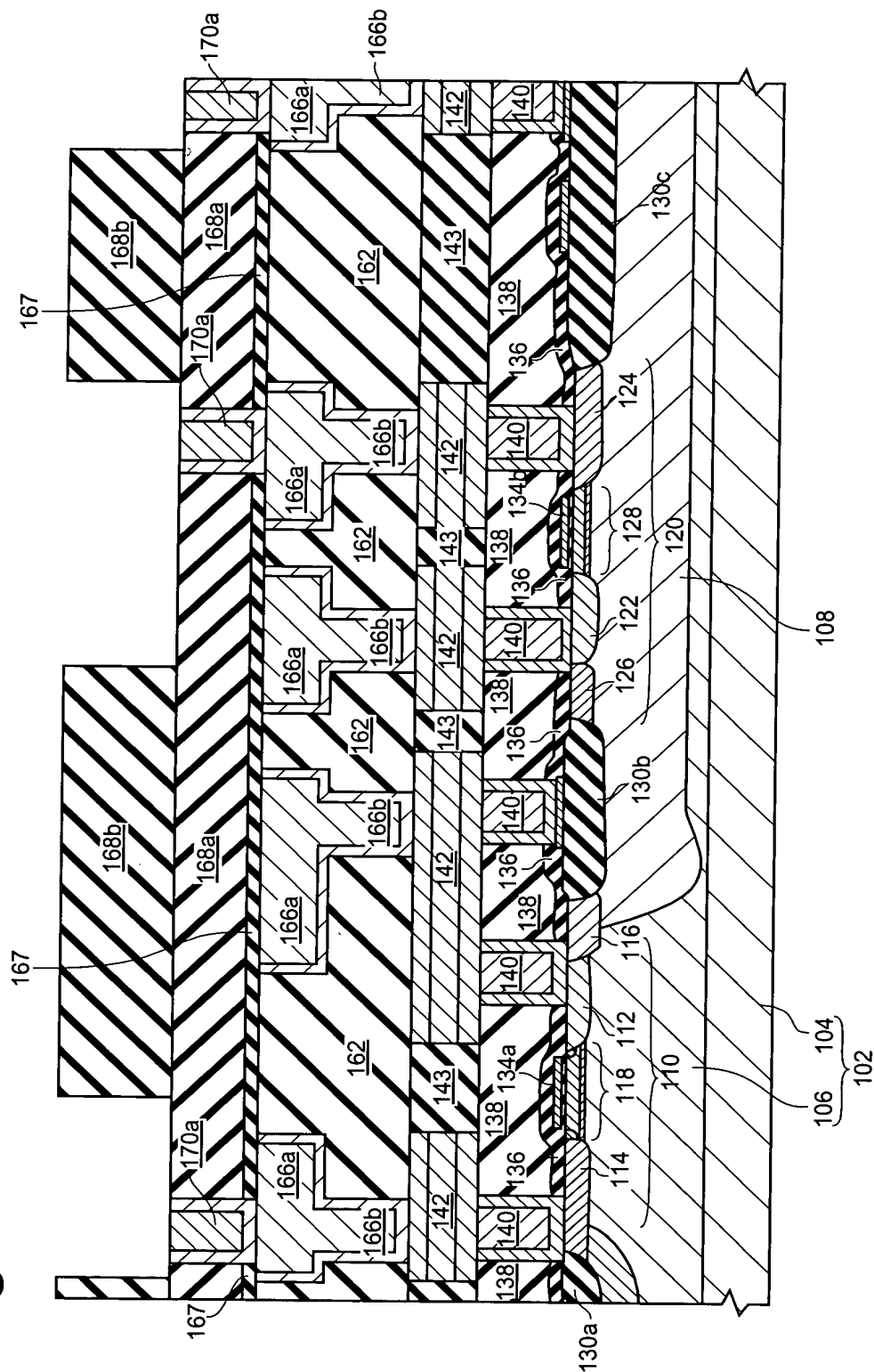


Fig. 14

